**Guidelines for EDTM Paper**

**with 14-pt Title even for 2 Rows**

Kazunari Ishimaru1, Masumi Saitoh1, Masaharu Kobayashi2, Kensuke Ota1,

Iriya Muneta3, Hitoshi Wakabayashi3, and Shuji Ikeda4

1Kioxia Corporation, Tokyo, Japan, edtm@jtbcom.co.jp

2The University of Tokyo, 3Tokyo Institute of Technology, 4tei Solutions

**Abstract**

This abstract is a brief (75 words) synopsis of your **3-page** **camera-ready** paper.

(Keywords: Manufacturing, CMOS and SOI)

**Introduction**

This template has been tailored for output on A4- or letter-sized paper. Margins, column widths, line spacing, and type styles are built-in; examples of the type styles are provided throughout this document and are identified in italic type, within parentheses, following the example, for the Electron Devices Technology and Manufacturing conference (EDTM) [1]. Final camera ready 3-page paper of text with 2 columns, figures and tables should be submitted by October 18, 2021. The paper should explain why/how it was done, principal results, and their significances.

**Formats and Fonts**

14, 12 and 11 pt of Times New Roman are used for the title, author/affiliation and text, respectively. In particular, the use of the International System of Units (SI Units) is advocated. And use a zero before decimal points: “0.25”, not “.25”.

*A. Equations*

11-pt Italic of Times New Roman is used for the equation, as shown in Eq. (1). The number of equation within parentheses are to position flush right.

*y = f(x)* (1)

*B. References*

When referring to them in the text, type the corresponding reference number in square brackets as shown at the end of this sentence [1].

*C. Table*

10.5 pt of Times New Roman is used for the caption, as shown in Table 1.

*D. Figure*

Note that the digest of EDTM will be provided as an electronic information through the USB. However, maximum 10 figures are recommended to find the achievements of your work. 10.5 pt of Times New Roman is also used for the caption.

**Conclusion**

Summarize the contents of paper. And finally, don't forget to check the spelling.

**Acknowledgments**

The authors gratefully acknowledge the contributions of T. Edison, G. Westinghouse, N. Tesla, A. Volta and A. Ampere to the electric power industry.

**References**

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Table 1: List of font sizes.

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| --- | --- | --- |
| Text | Type | Font [pt] |
| Title | Bold | 14 |
| Authors |  | 12 |
| Affiliation |  | 12 |
| Headings | Bold | 11 |
| *Sub-headings* | Italic | 11 |
| Main text |  | 11 |
| *Equation* | Italic | 11 |
| References |  | 10.5 |
| Footnotes |  | 10.5 |
| Table caption |  | 10.5 |
| Figure caption |  | 10.5 |



Fig. 1: Logos of the IEEE, EDS, and EDTM 2022.